

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In the Patent Application of

Takashi NOGUCHI et al.

Serial No.: To Be Assigned

Art Unit: 2813

Filed: January 8, 2004

Examiner: Jack S. J. Chen

For: METHOD OF FORMING N-AND P-CHANNEL  
FIELD EFFECT TRANSISTORS ON THE SAME  
SILICON LAYER HAVING A STREAM EFFECT

**CLAIM TO PRIORITY UNDER 35 U.S.C. 119**

Commissioner for Patents  
P.O. Box 1450  
Washington, D.C. 20231

Sir:

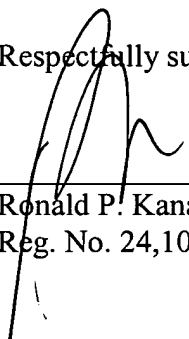
The benefit of the filing dates of the following prior applications filed in the following foreign country is hereby requested and the right of priority provided under 35 U.S.C. §119 is hereby claimed:

**Japanese Patent Appln. No. P09-074746 filed March 27, 1997**

In support of this claim, filed within parent application Serial No. 09/048,288 is a certified copy of said original foreign application.

Respectfully submitted,

Dated: January 8, 2004

  
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